

HCG600FH120D3ME7

1200V/600A Half Bridge IGBT Module

Description

The HCG600FH120D3ME7 is a Half Bridge IGBT Power Module. It integrates high performance IGBT chips designed for the applications such as High Power supply and Motor control.

Features

- Blocking voltage:1200V
- Low saturation voltage $V_{CE(sat)}$
- Low Switching Losses
- Thermistor inside

Applications

- High Power Switching Applications
- Motor Drives
- Solar inverter Systems
- Uninterrupted Power Supply



Circuit diagram

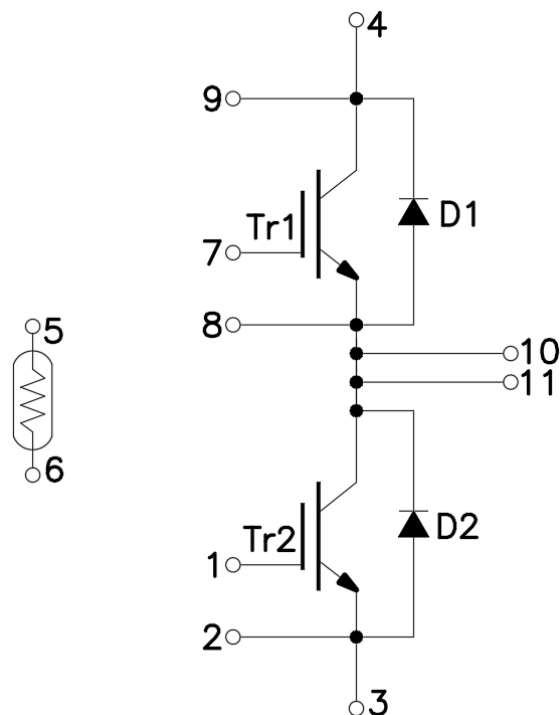


Figure 1. Out drawing & circuit diagram for HCG600FH120D3ME7

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Pin Configuration and Marking Information

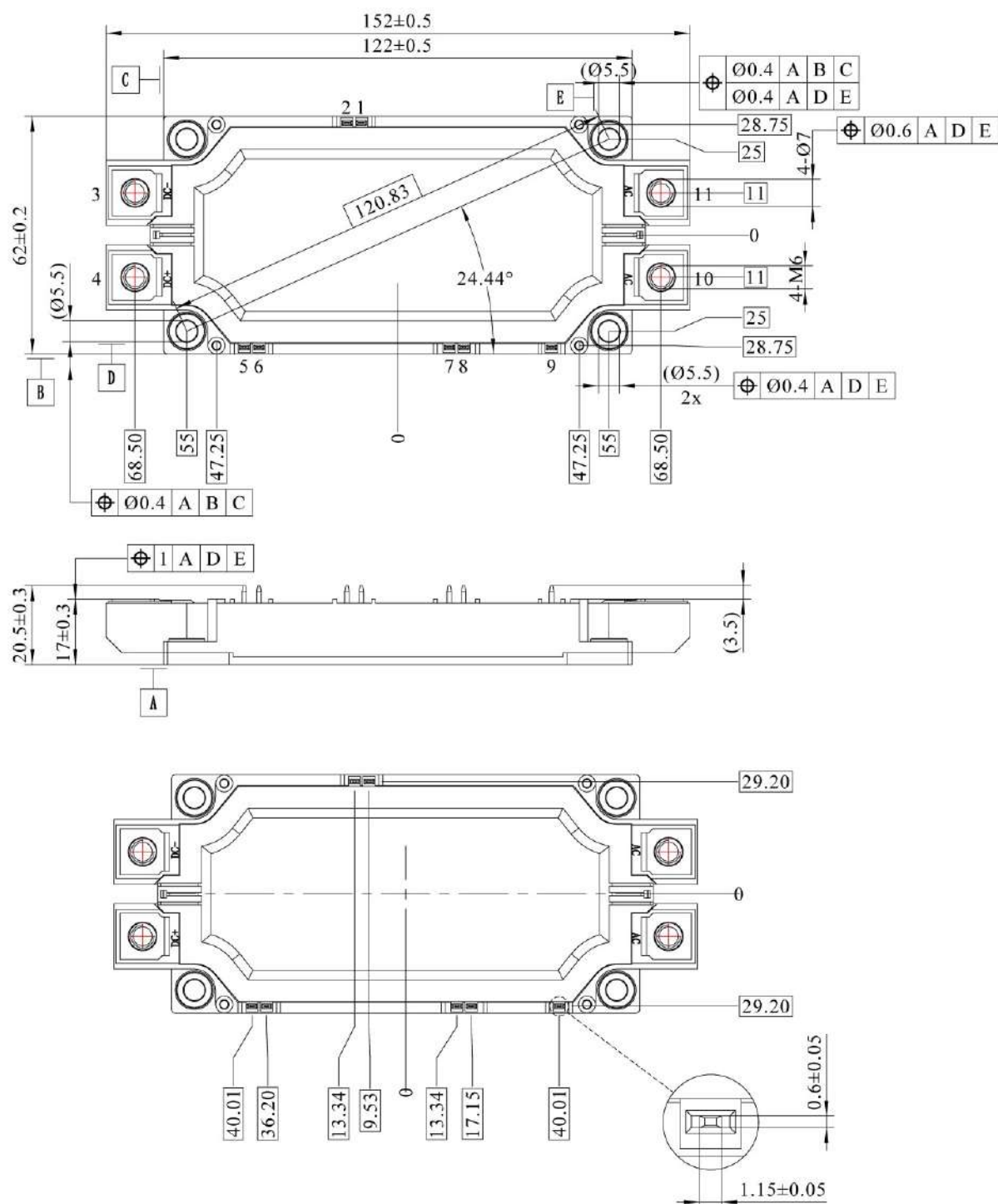


Figure 2. Pin configuration

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Module

Parameter	Condition	Value	Unit
Isolation Voltage	RMS, f = 50Hz, t = 1min	3.4	kV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 13	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	600	-
Module lead resistance, terminals – chip	T _C = 25°C	0.8	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	350	g

Maximum Ratings (T_j = 25 °C unless otherwise specified)

Symbol	Parameter	Condition	Ratings	Unit
V _{CES}	Collector-Emitter Voltage	G-E Short	1200	V
V _{GES}	Gate-Emitter Voltage	C-E Short	±20	V
I _C	DC Continuous Collector Current	T _C = 95°C	600	A
I _{CM}	Pulse Collector Current	t _p = 1ms, Note1	1200	A
P _C	Maximum Power Dissipation	T _C = 25°C, IGBT	3000	W
I _F	Diode Forward Current	-	600	A
I _{FRM}	Repetitive peak forward Current	t _p = 1ms, Note1	1200	A
T _{vjop}	Operating junction temperature	Note2	-40 to 175	°C
T _{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

Note2: T_{vjop} > 150°C is only allowed for operation at overload conditions

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _C = 25°C	-	5	-	kΩ
$\frac{\Delta R}{R}$	Deviation of R ₁₀₀	T _C = 100°C, R ₁₀₀ = 493 Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C = 25°C	-	-	20	mW
B _{25/50}	B-value	R ₂ = R ₂₅ exp [B _{25/50} (1/T ₂ - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R ₂ = R ₂₅ exp [B _{25/80} (1/T ₂ - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R ₂ = R ₂₅ exp [B _{25/100} (1/T ₂ - 1/(298,15 K))]	-	3433	-	K

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IGBT Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max.	
V _{CE(sat)} (Chip)	Collector-Emitter Saturation Voltage	I _C =600A V _{GE} =15V	T _j =25°C	-	1.60	1.92	V
			T _j =125°C	-	1.73	-	
			T _j =150°C	-	1.80	-	
			T _j =175°C	-	1.85	-	
V _{GE(th)}	Gate-Emitter threshold Voltage	I _C =23mA, V _{CE} =V _{GE}		5.0	5.8	6.5	V
Q _G	Gate charge	V _{GE} = -15V to +15V		-	6.9	-	uC
R _{Gint}	Internal gate resistor	-	T _j =25°C	-	0.53	-	Ω
C _{ies}	Input Capacitance	V _{CE} =25V	T _j =25°C	-	86.4	-	nF
C _{oes}	Output Capacitance	V _{GE} =0V		-	2.35	-	nF
C _{res}	Reverse transfer Capacitance	f =1MHz		-	0.66	-	nF
I _{CES}	Collector- Emitter Cut off Current	V _{CE} =1200V, V _{GE} =0V	T _j =25°C	-	-	1	mA
I _{GES}	Gate-Emitter Leakage Current	V _{GE} = 20V, V _{CE} =0V	T _j =25°C	-	-	1	uA
t _{d(on)}	Turn-on delay time	V _{CC} =600V I _C =600A V _{GE} =+15V/-8V R _G =1.0Ω Inductive load	T _j =25°C	-	222	-	ns
			T _j =125°C	-	196	-	
			T _j =150°C	-	196	-	
t _r	Rise time		T _j =25°C	-	56	-	ns
			T _j =125°C	-	58	-	
			T _j =150°C	-	63	-	
t _{d(off)}	Turn-off delay time		T _j =25°C	-	690	-	ns
			T _j =125°C	-	861	-	
			T _j =150°C	-	924	-	
t _f	Fall time		T _j =25°C	-	144	-	ns
			T _j =125°C	-	273	-	
			T _j =150°C	-	302	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	26.62	-	mJ
			T _j =125°C	-	36.97	-	
			T _j =150°C	-	45.01	-	
E _{off}	Turn-off power dissipation		T _j =25°C	-	42.61	-	mJ
		T _j =125°C	-	77.19	-		
		T _j =150°C	-	80.63	-		
R _{th(j-c)}	Thermal Resistance, Junction to Case (IGBT)			-	0.05	-	°C/W
R _{th(c-s)}	Thermal Resistance, Case to sink (Conductive Grease applied) , Note1			-	0.015	-	°C/W

Note1: Assumes Thermal Conductivity of grease is 2.8 W/m · K and thickness is 50um

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Freewheeling Diode Electrical characteristics ($T_j=25^{\circ}\text{C}$ unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max.	
V _F	Diode Forward Voltage	I _F =600A, V _{GE} =0V	T _j =25°C	-	1.64	1.97	V
			T _j =125°C	-	1.48	-	
			T _j =150°C	-	1.49	-	
			T _j =175°C	-	1.44	-	
t _{rr}	Reverse recovery time	(Switch side) V _{CC} =600V	T _j =25°C	-	0.566	-	us
			T _j =125°C	-	0.858	-	
			T _j =150°C	-	0.944	-	
I _{RM}	Peak reverse recovery Current	I _C =600A V _{GE} =+15V/-8V R _G =1.0Ω	T _j =25°C	-	382	-	A
			T _j =125°C	-	495	-	
			T _j =150°C	-	521	-	
Q _{rr}	Recovered charge	(FRD side) V _{rr} =600V I _F =600A V _{GE} =-8V	T _j =25°C	-	88.32	-	uC
			T _j =125°C	-	161.9	-	
			T _j =150°C	-	183.6	-	
E _{rr}	Reverse recovered energy	Inductive load switching operation	T _j =25°C	-	41.55	-	mJ
			T _j =125°C	-	75.71	-	
			T _j =150°C	-	85.68	-	
R _{th(j-c)}	Thermal Resistance, Junction to Case (Diode)			-	0.07	-	°C/W
R _{th(c-s)}	Thermal Resistance, Case to sink (Conductive Grease applied) , Note1			-	0.02	-	°C/W

Note1: Assumes Thermal Conductivity of grease is $2.8 \text{ W/m} \cdot \text{K}$ and thickness is $50\mu\text{m}$

Test Conditions

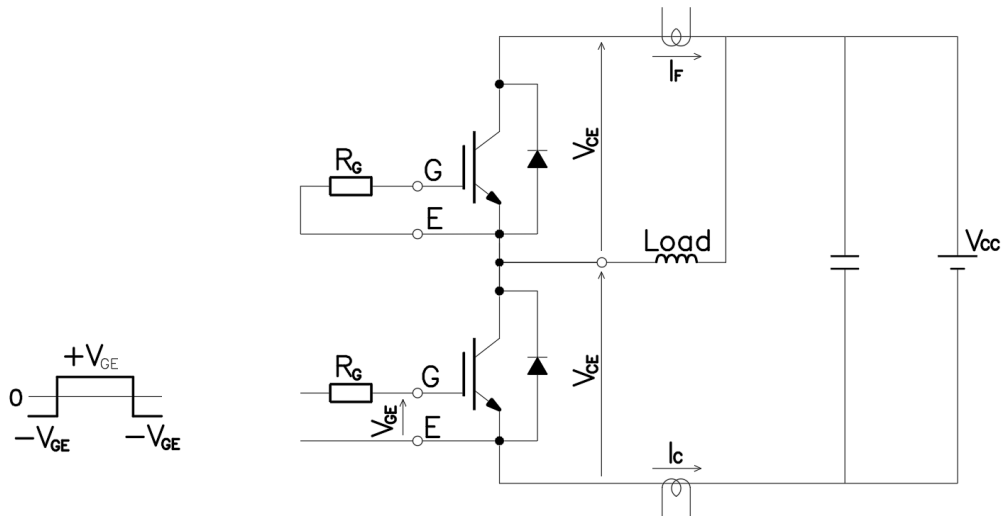


Figure 3. Switching time measure circuit

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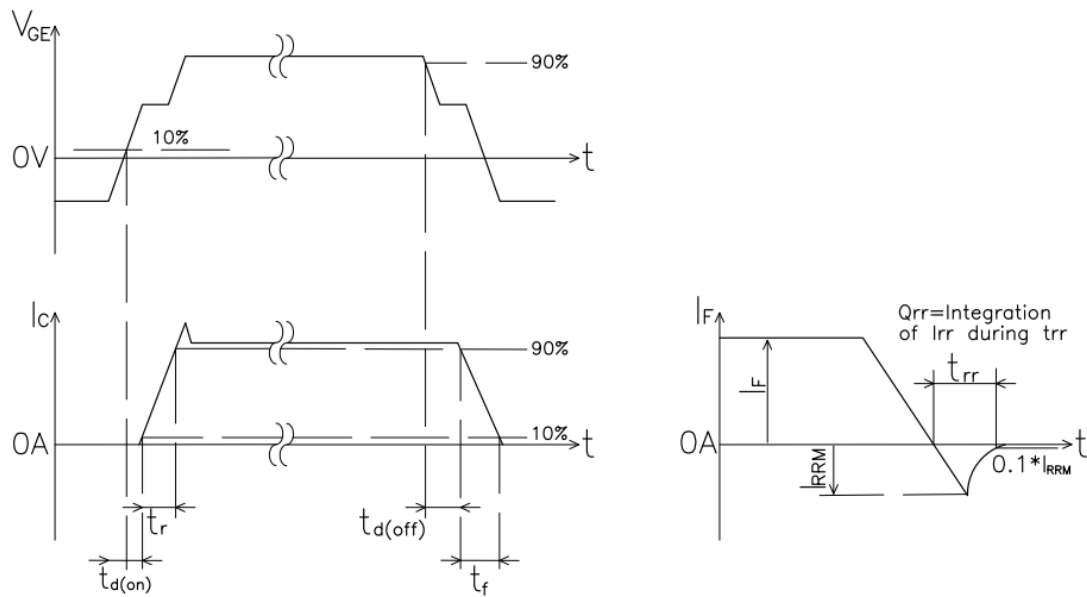


Figure 4. Switching time definition

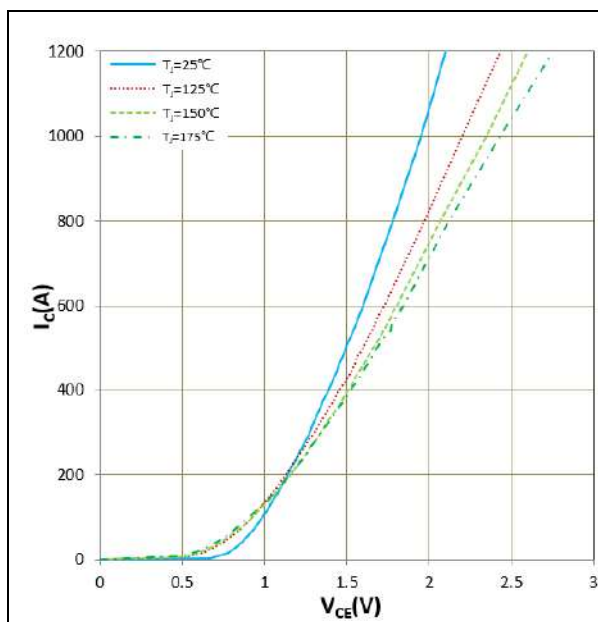


Figure 5. I_C vs V_{CE}
 $V_{GE}=15V$

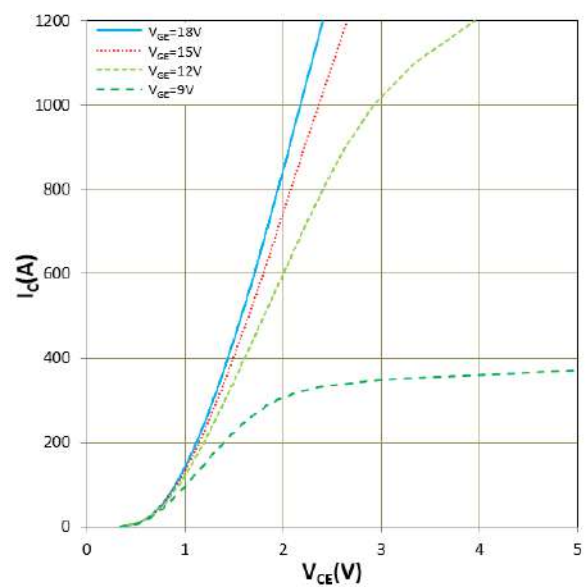


Figure 6. I_C vs V_{CE}
 $T_j=150^{\circ}C$

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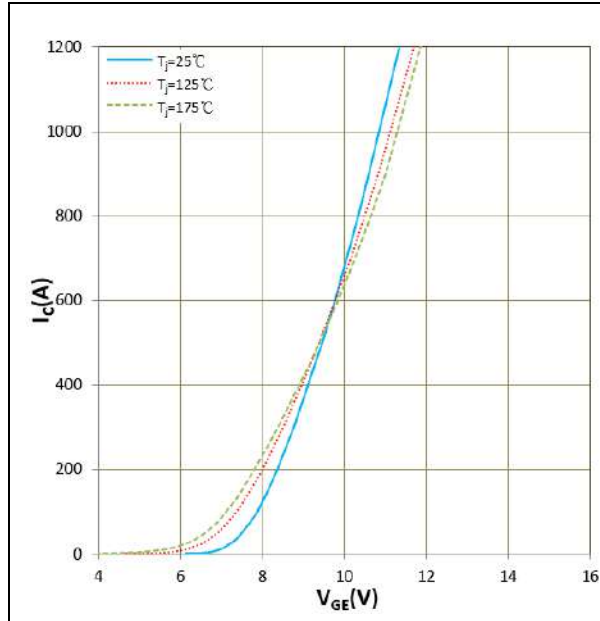


Figure 7. I_c vs V_{GE}
 $V_{CE} = 20\text{V}$

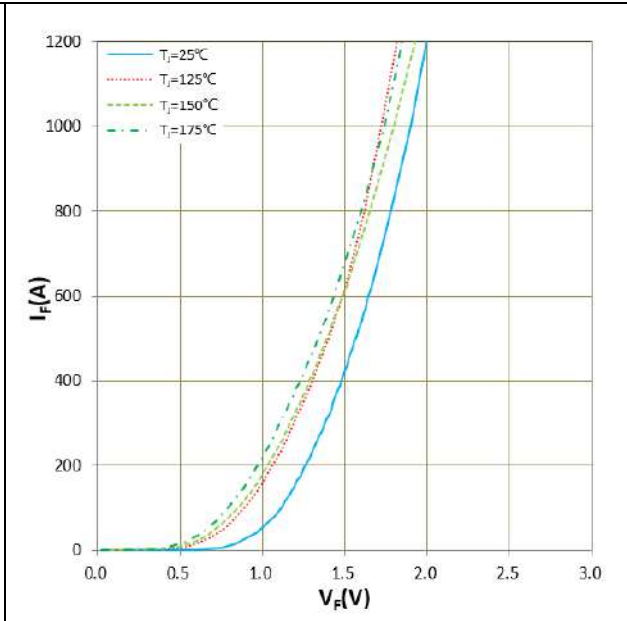


Figure 8. I_F vs V_F

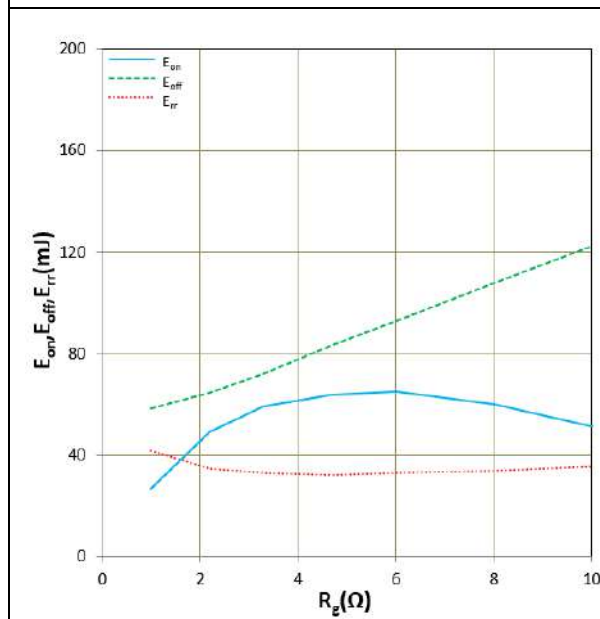


Figure 9. E_{on} , E_{off} , E_{tr} vs R_g (Typ)
 $V_{CC} = 600\text{V}$, $V_{GE} = +15\text{V}/-8\text{V}$, $I_c = 600\text{A}$, $T_j = 25^\circ\text{C}$
Inductive Load

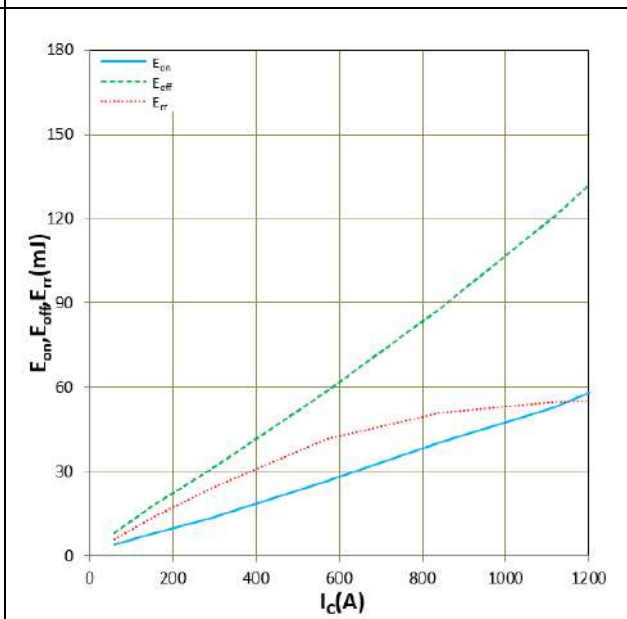


Figure 10. E_{on} , E_{off} , E_{tr} vs I_c (Typ)
 $V_{CC} = 600\text{V}$, $V_{GE} = +15\text{V}/-8\text{V}$, $R_g = 1.0\Omega$, $T_j = 25^\circ\text{C}$
Inductive Load

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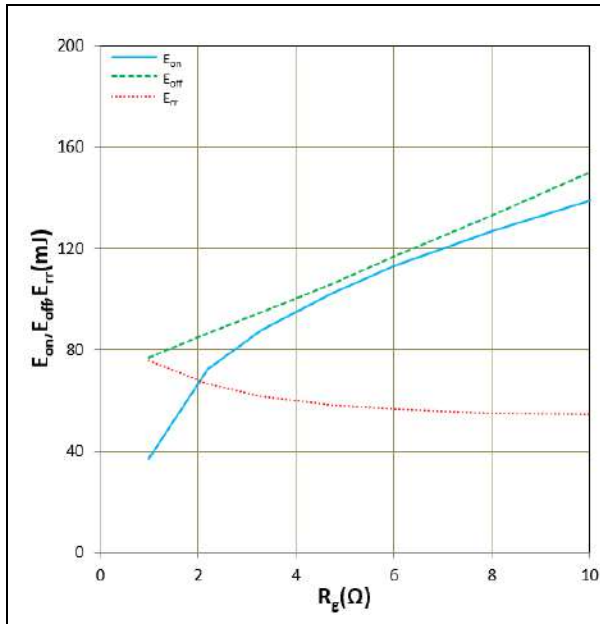


Figure 11. E_{on} , E_{off} , E_{rr} vs R_g (Typ)
 $V_{CC}=600V$, $V_{GE}=+15V/-8V$, $I_C=600A$, $T_j=125^\circ C$
 Inductive Load

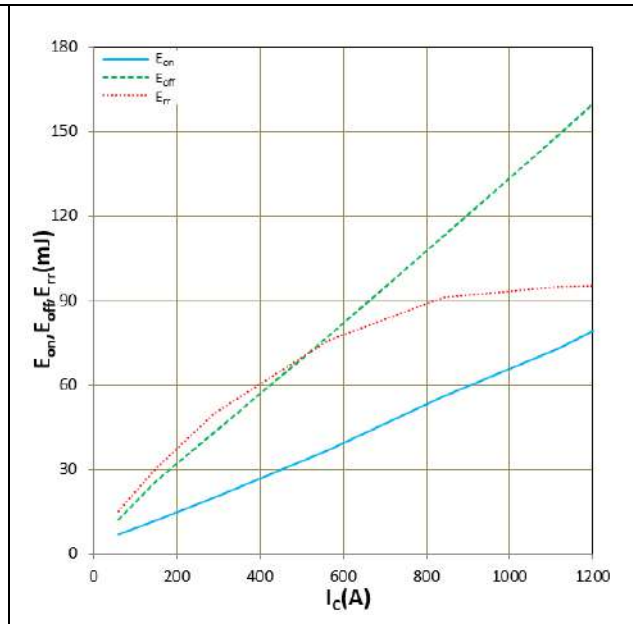


Figure 12. E_{on} , E_{off} , E_{rr} vs I_c (Typ)
 $V_{CC}=600V$, $V_{GE}=+15V/-8V$, $R_g=1.0\Omega$, $T_j=125^\circ C$
 Inductive Load

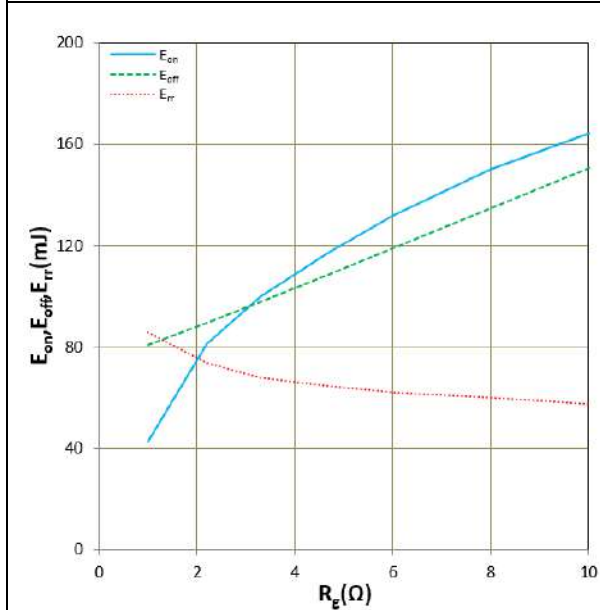


Figure 13. E_{on} , E_{off} , E_{rr} vs R_g (Typ)
 $V_{CC}=600V$, $V_{GE}=+15V/-8V$, $I_C=600A$, $T_j=150^\circ C$
 Inductive Load

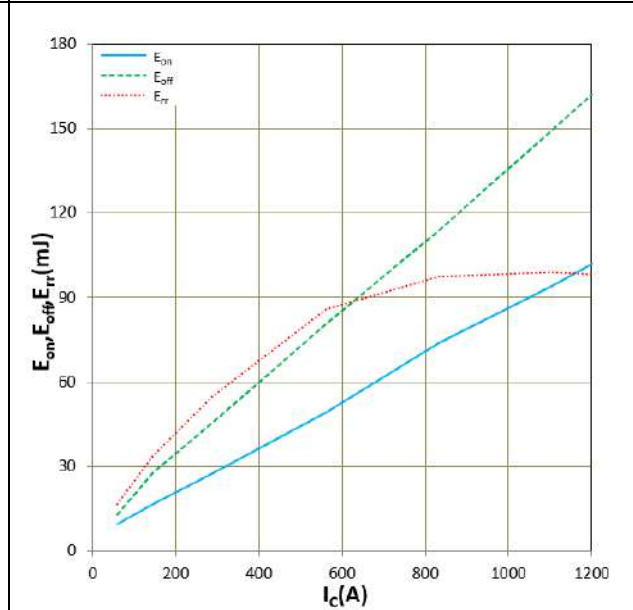


Figure 14. E_{on} , E_{off} , E_{rr} vs I_c (Typ)
 $V_{CC}=600V$, $V_{GE}=+15V/-8V$, $R_g=1.0\Omega$, $T_j=150^\circ C$
 Inductive Load

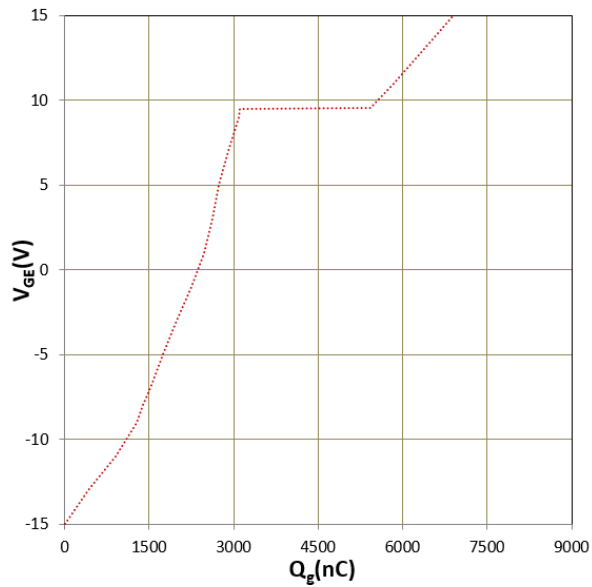
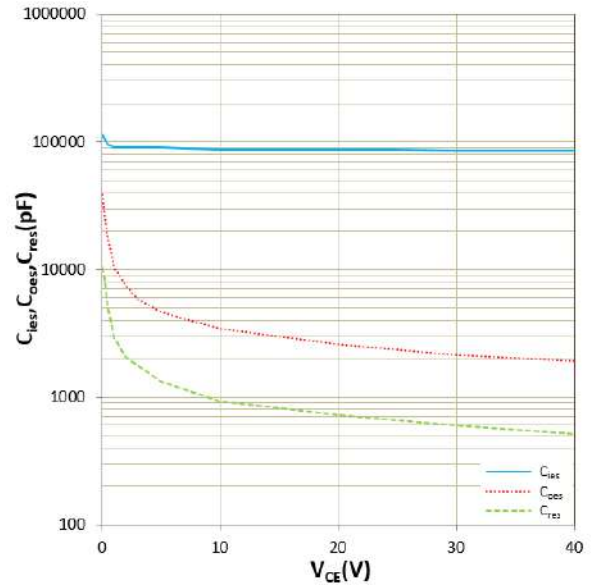
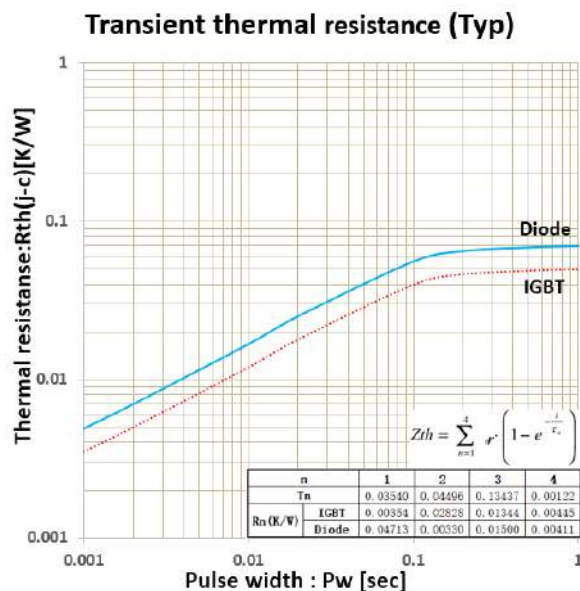


Figure 15. Gate charge


Figure 16. C_{ies} , C_{oes} , C_{res} vs V_{CE}
 $T_j = 25^\circ\text{C}$, $f = 1\text{MHz}$

Figure 17. transient thermal impedance
IGBT/Diode

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This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

The data contained in this document is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the product's suitability for the intended application and the completeness of the product data concerning such application.

Due to technical requirements, our product may contain dangerous substances. For information on the types in question, please contact the sales staff responsible for you.

Changes to this product data sheet are reserved.

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Revision History

Document Version	Description of Changes
RevX.0.1	Released

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